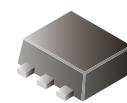


CDSH6-4448-G RoHS Device



Features

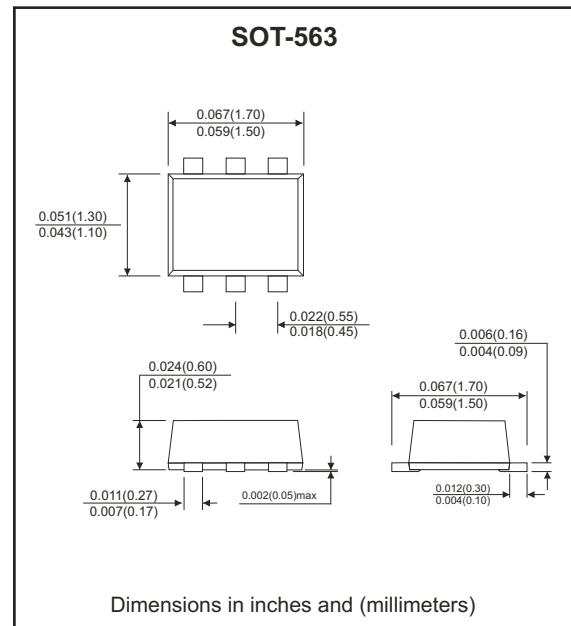
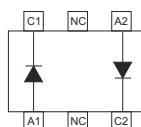
- Fast Switching Speed
- For general purpose switching applications.
- High conductance.

Mechanical data

- Case: SOT-563, Molded Plastic
- Terminals: Solderable per MIL-STD-202, Method 208

Marking: KAL

Circuit diagram



Maximum Ratings (at TA=25°C unless otherwise noted)

Parameter	Symbol	Max	Unit
Non-repetitive peak reverse voltage	V _{RM}	100	V
Peak repetitive peak reverse voltage	V _{RRM}		
Working peak reverse voltage	V _{RWM}	80	V
DC blocking voltage	V _R		
RMS reverse voltage	V _{R(RMS)}	57	V
Forward continuous current	I _{FM}	500	mA
Averaged rectified output current	I _O	250	mA
Peak forward surge current @t=1.0μs @T=1.0s	I _{FSM}	4 2	A
Power dissipation	P _D	150	mW
Thermal resistance, junction to air	R _{θJA}	833	°C/W
Junction temperature	T _J	150	°C
Storage temperature	T _{STG}	-65 to +150	°C

Electrical Characteristics (at TA=25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Max	Unit
Reverse breakdown voltage	I _R =2.5μA	V _{BR}	80		V
Reverse voltage leakage current	V _R =70V V _R =20V	I _R		0.1 25	μA nA
Forward voltage	I _F =5mA I _F =10mA I _F =100mA I _F =150mA	V _F	0.62	0.72 0.855 1 1.25	V
Diode capacitance	V _R =6V, f=1MHz	C _T		3.5	pF
Reverse recovery time	I _F =I _R =10mA, I _{rr} =0.1×I _R , R _L =100Ω	t _{rr}		4	nS

SMD Switching Diode

Comchip
SMD Diode Specialist

Typical Characteristics (CDSH6-4448-G)

Fig.1 - Forward Power Derating Curve

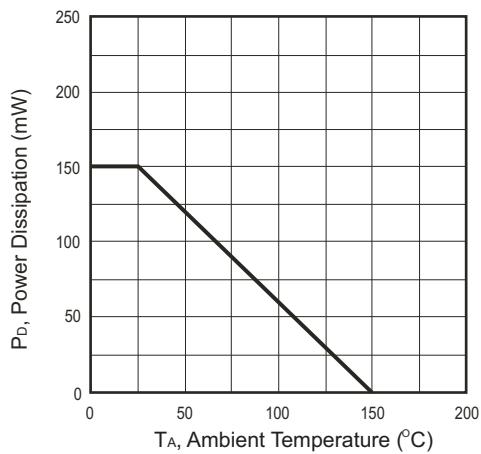


Fig.2 - Typical Forward Characteristics

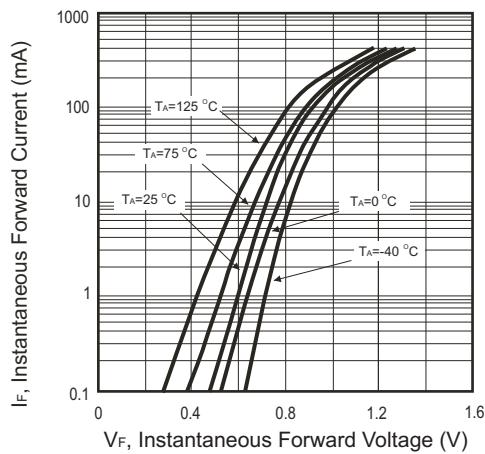


Fig.3 - Typical Diode Capacitance Characteristics

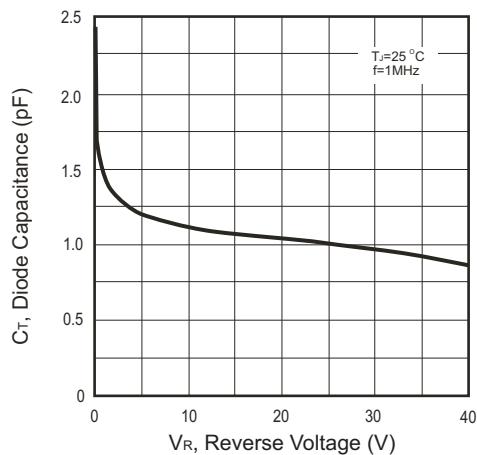


Fig.4 - Typical Reverse Current Characteristics

